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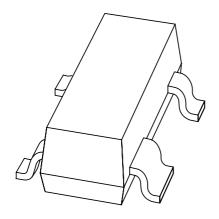
If you have any questions related to the data sheet, please contact our nearest sales office via e-mail or telephone (details via **salesaddresses@nexperia.com**). Thank you for your cooperation and understanding,

Kind regards,

Team Nexperia

DISCRETE SEMICONDUCTORS

DATA SHEET



BAW101 High voltage double diode

Product data sheet

2003 May 13



High voltage double diode

BAW101

FEATURES

- Small plastic SMD package
- High switching speed: max. 50 ns
- High continuous reverse voltage: 300 V
- Electrically insulated diodes.

APPLICATIONS

- · High voltage switching
- Automotive
- Communication.

DESCRIPTION

The BAW101 is a high-speed switching diode array with two separate dice, fabricated in planar technology and encapsulated in a small SOT143B plastic SMD package.

MARKING

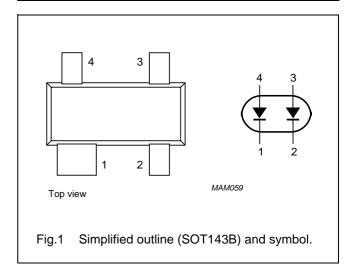
TYPE NUMBER	MARKING CODE(1)			
BAW101	*AB			

Note

- 1. * = p: Made in Hong Kong.
 - * = t: Made in Malaysia.
 - * = W: Made in China.

PINNING

PIN	DESCRIPTION				
1	cathode 1				
2	cathode 2				
3	anode 2				
4	anode 1				



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High voltage double diode

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LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT					
Per diode	Per diode									
V _R	continuous reverse voltage		_	300	V					
		series connection	_	600	V					
V_{RRM}	repetitive peak reverse voltage		_	300	V					
		series connection	_	600	V					
I _F	continuous forward current	single diode loaded; note 1; see Fig.2	_	250	mA					
		double diode loaded; note 1; see Fig.2	_	140	mA					
I _{FRM}	repetitive peak forward current		_	625	mA					
I _{FSM}	non-repetitive peak forward current	square wave; $T_j = 25$ °C prior to surge; $t = 1 \mu s$	_	4.5	А					
P _{tot}	total power dissipation	T _{amb} = 25 °C; note 1	_	350	mW					
T _{stg}	storage temperature		-65	+150	°C					
Tj	junction temperature		_	150	°C					
T _{amb}	operating ambient temperature		-65	+150	°C					

Note

ELECTRICAL CHARACTERISTICS

 $T_j = 25$ °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
Per diode					
V _{BR(R)}	reverse breakdown voltage	I _R = 100 μA	300	_	V
V _F	forward voltage	I _F = 100 mA; note 1	_	1.1	V
I _R	reverse current	V _R = 250 V	_	150	nA
		V _R = 250 V; T _{amb} = 150 °C	_	50	μΑ
t _{rr}	reverse recovery time	when switched from I_F = 30 mA to I_R = 30 mA; R_L = 100 Ω ; measured at I_R = 3 mA	_	50	ns
C _d	diode capacitance	V _R = 0 V; f = 1 MHz	_	2	pF

Note

1. Pulse test: pulse width = 300 μ s; δ = 0.02.

^{1.} Device mounted on an FR4 printed-circuit board, cathode-lead mounting pad = 1 cm².

High voltage double diode

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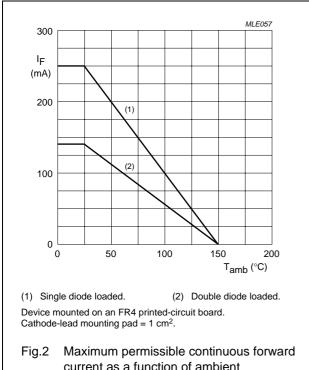
THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R _{th j-s}	thermal resistance from junction to soldering point	note 1	255	K/W
R _{th j-a}	thermal resistance from junction to ambient	note 2	357	K/W

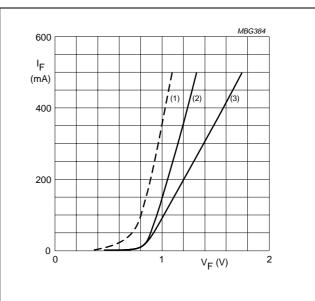
Notes

- 1. One or more diodes loaded.
- 2. Device mounted on an FR4 printed-circuit board, cathode-lead mounting pad = 1 cm².

GRAPHICAL DATA



current as a function of ambient temperature.



- (1) $T_j = 150$ °C; typical values.
- (2) $T_j = 25$ °C; typical values.

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(3) $T_j = 25$ °C; maximum values.

Fig.3 Forward current as a function of forward voltage.

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High voltage double diode

BAW101

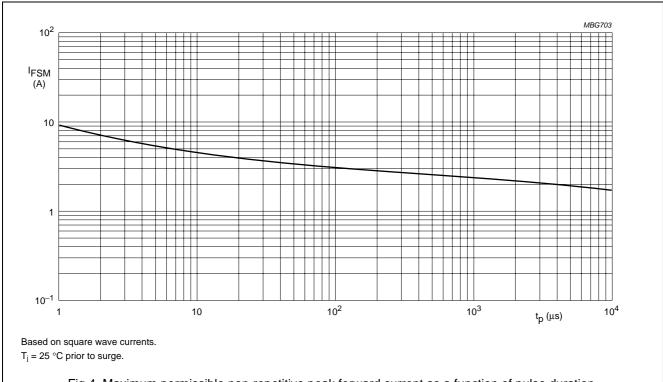
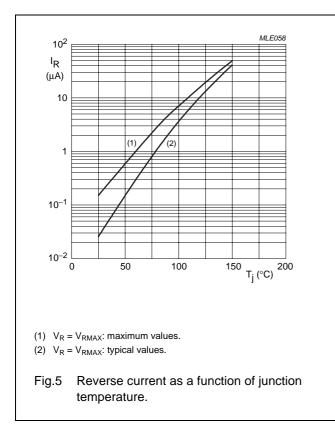
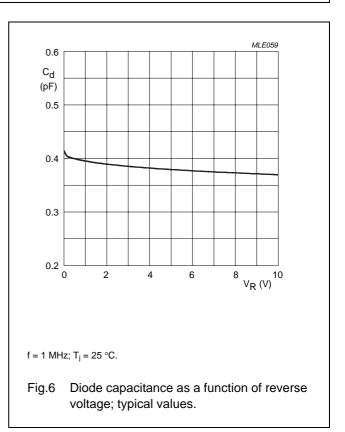


Fig.4 Maximum permissible non-repetitive peak forward current as a function of pulse duration.

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High voltage double diode

BAW101

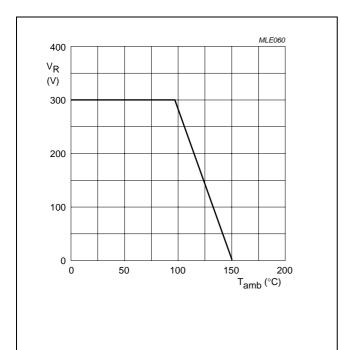


Fig.7 Maximum permissible continuous reverse voltage as a function of ambient temperature.

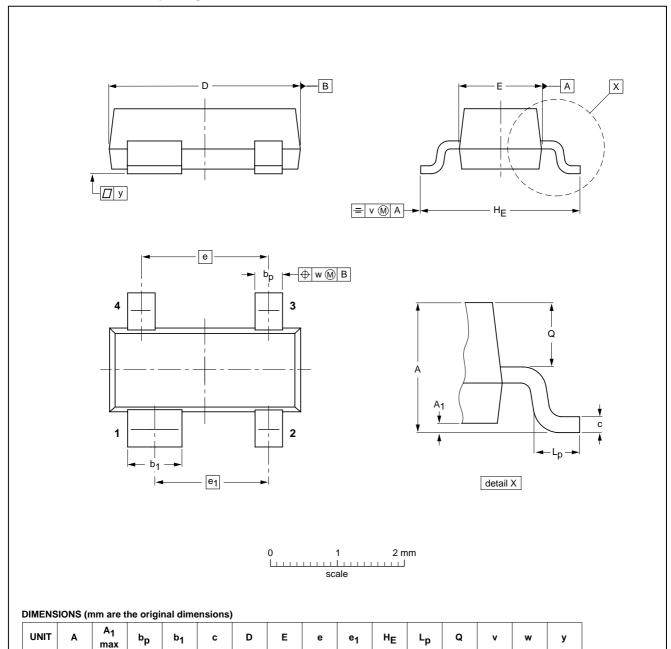
High voltage double diode

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PACKAGE OUTLINE

Plastic surface mounted package; 4 leads

SOT143B



PETERNOTO															
	0.9		0.38	0.78	0.09	2.8	1.2	1.0		2.1	0.15	0.45	0.2	0.1	0.1
mm	1.1	0.1	0.48	0.88	0.15	3.0	1.4	1.9	1.7	2.5	0.45	0.55	0.2	0.1	0.1

OUTLINE		REFER	EUROPEAN	ISSUE DATE		
VERSION	IEC	JEDEC	EIAJ		PROJECTION	ISSUE DATE
SOT143B						97-02-28

High voltage double diode

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DATA SHEET STATUS

DOCUMENT STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

Notes

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NXP Semiconductors

Customer notification

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Contact information

For additional information please visit: http://www.nxp.com

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